

P-Ch 30V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology



Product Summary

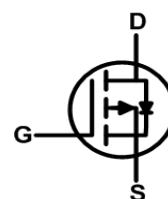
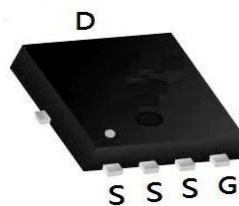
BVDSS	RDSON	ID
-30V	8.5 mΩ	-55A

Description

The UD3419A is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The UD3419A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN3333-8L Pin Configuration



Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _C = 25°C	-55	A
		T _C = 100°C	-23	A
I _{DM}	Pulsed Drain Current ^{note1}		-140	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}		78.8	mJ
P _D	Power Dissipation	T _C = 25°C	21.5	W
R _{θJC}	Thermal Resistance, Junction to Case		5.8	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =-10V, I _D =-12A	-	8.5	11	mΩ
		V _{GS} =-4.5V, I _D =-8A	-	13	18	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	-	2800	-	pF
C _{oss}	Output Capacitance		-	346	-	pF
C _{rss}	Reverse Transfer Capacitance		-	319	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -20A, V _{GS} = -10V	-	30	-	nC
Q _{gs}	Gate-Source Charge		-	5.3	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	7.6	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -20A, V _{GS} =-10V, R _{GEN} =2.5Ω	-	14	-	ns
t _r	Turn-on Rise Time		-	20	-	ns
t _{d(off)}	Turn-off Delay Time		-	95	-	ns
t _f	Turn-off Fall Time		-	65	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-140	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -35A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J= 25°C, V_{DD}= -20V, V_G= -10V, L= 0.5mH, R_G= 25 Ω, I_{AS}= -17A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1: Output Characteristics

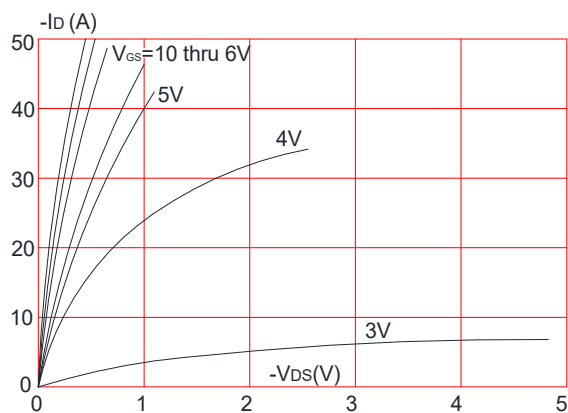


Figure 2: Typical Transfer Characteristics

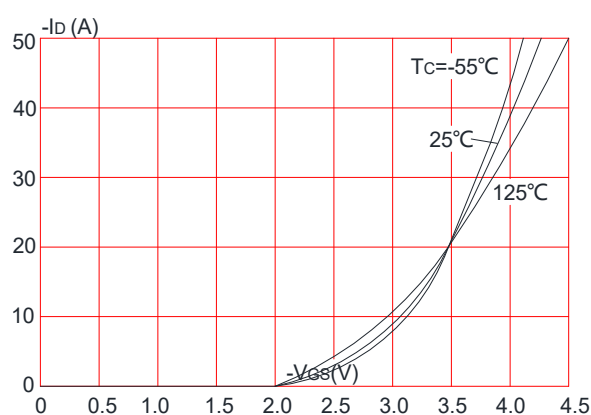


Figure 3: On-resistance vs. Drain Current

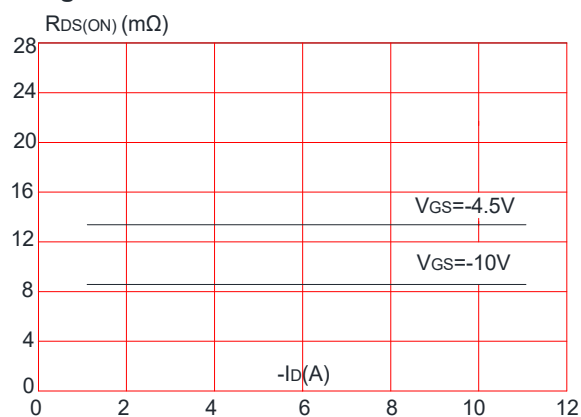


Figure 4: Body Diode Characteristics

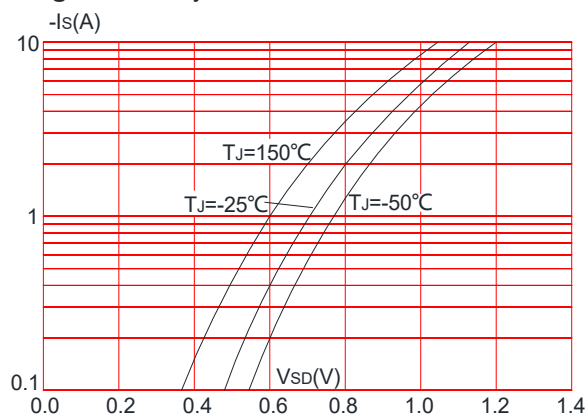


Figure 5: Gate Charge Characteristics

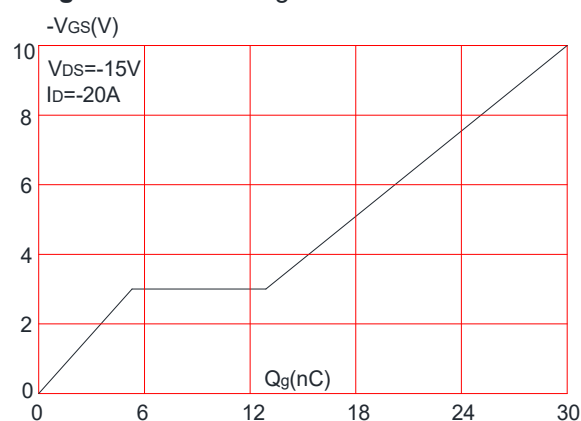
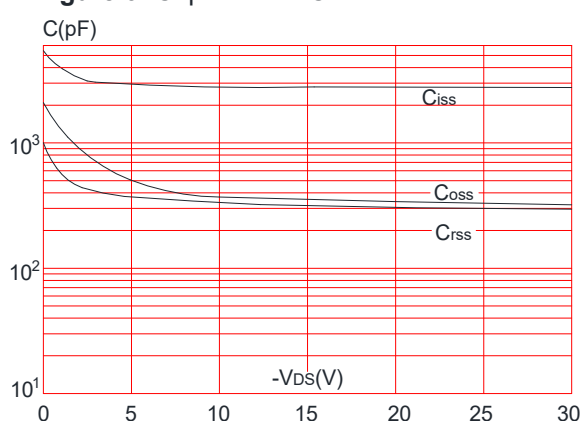


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

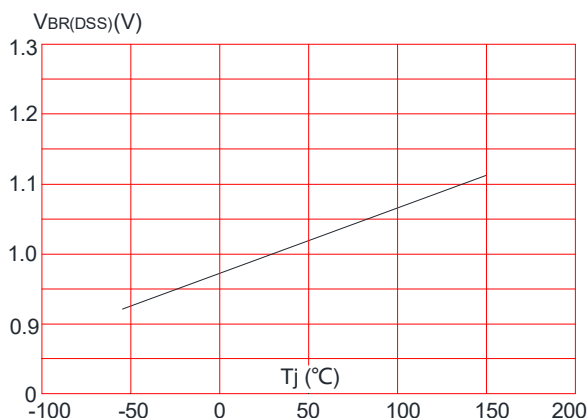


Figure 8: Normalized on Resistance vs. Junction Temperature

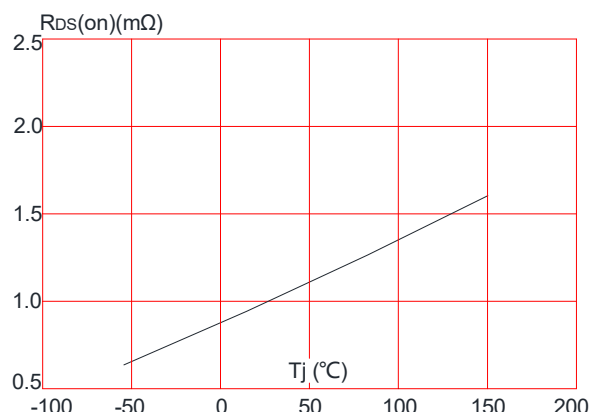


Figure 9: Maximum Safe Operating Area

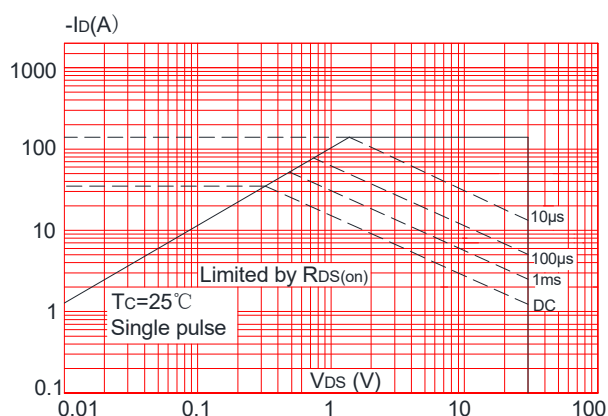


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

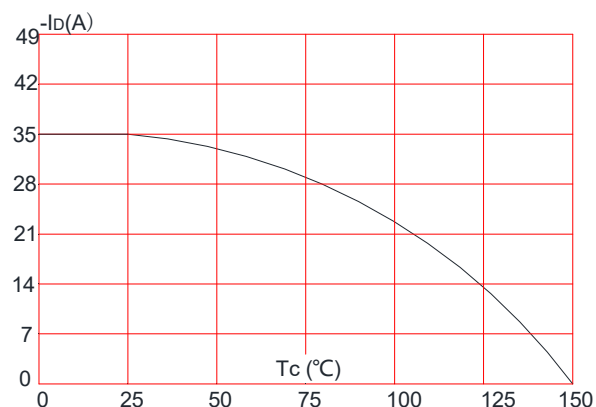
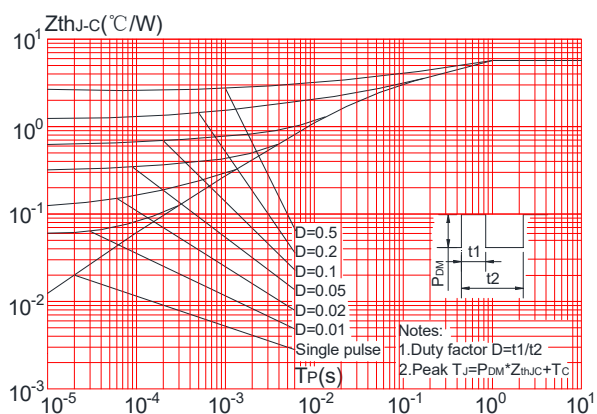
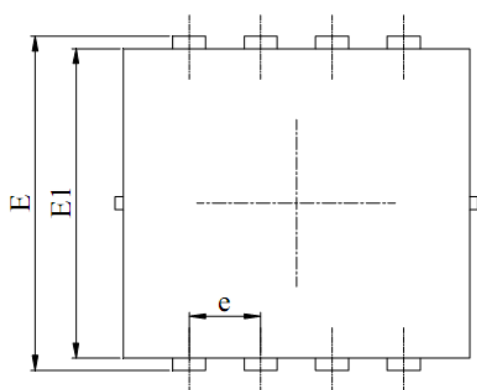


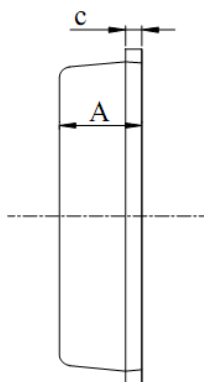
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



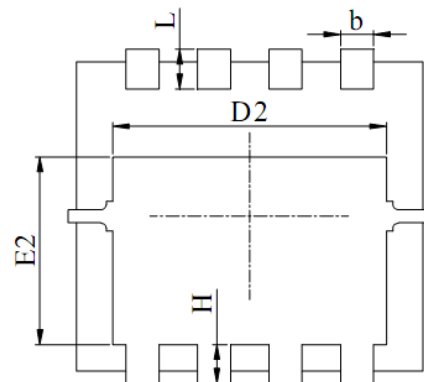
Package Mechanical Data-PDFN3333-8L-Single



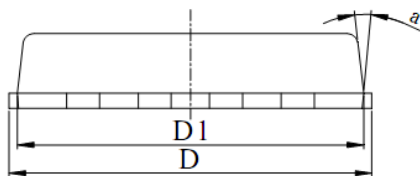
Top View



Side View



Bottom View

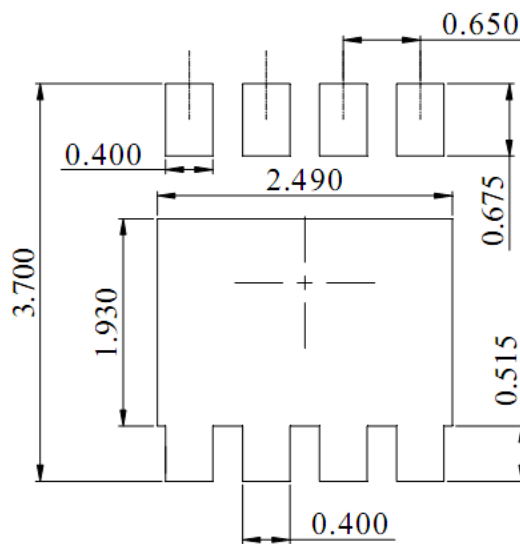


Front View

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS:MILLIMETERS